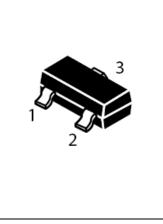
LITEON LITE-ON SEMICONDUCTORS

MMBT2907A

PNP General Purpose Transistor	COLLECTOR
FEATURES Ideal for Medium Power Amplification and Switching Complementary PNP Type available(MMBT2222A) 	1 BASE
 MECHANICAL DATA Case: SOT-23 Plastic Case material: "Green" molding compound, UL flammability classification 94V-0, (No Br. Sb. Cl) 	2 EMITTER

• Lead Free in RoHS 2002/95/EC Compliant

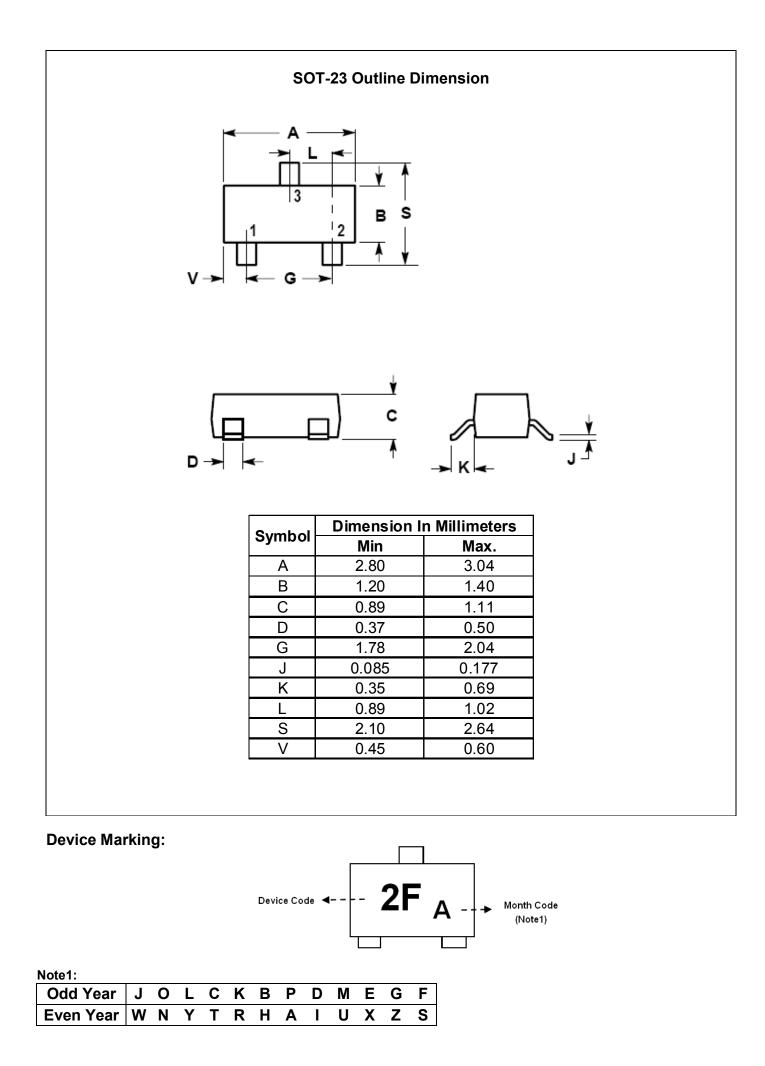


Maximum Ratings @ T_A = 25°C

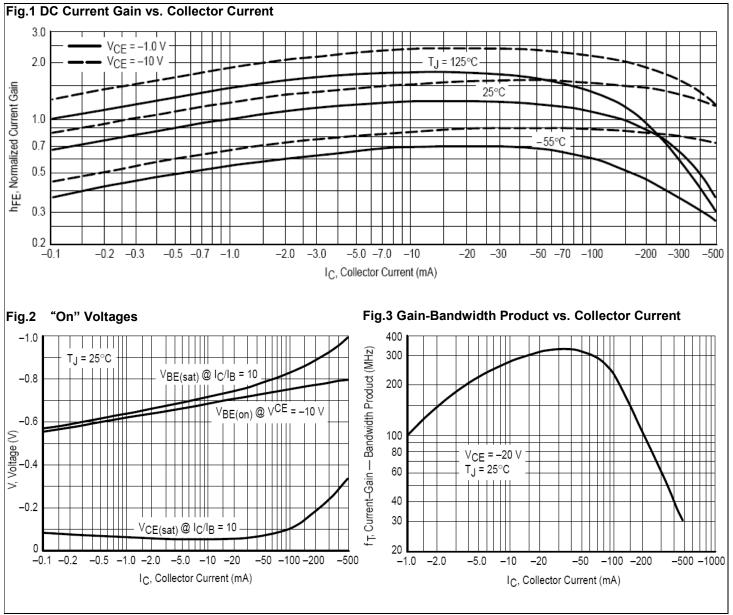
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current -Continuous	Ι _C	-600	mA
Collector Power Dissipation	Pc	250	mW
Thermal Resistance, junction to Ambient	Reja	500	°C /W
Junction Temperature	TJ	150	°C
Storage Temperature Range	T _{STG}	-55~+150	°C

Electrical Characteristics @ $T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Test Condition	Symbol	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	I _C =-10μΑ,I _E =0	V _{CBO}	-60			V
Collector-emitter breakdown voltage	I _C =-10mA,I _B =0	V _{CEO}	-60			V
Emitter-base breakdown voltage	I _E =-10μΑ,I _C =0	V_{EBO}	-5			V
Collector-base cut-off current	V _{CB} =-50V,I _E =0	I _{CBO}			-20	nA
Emitter-base cut-off current	V _{EB} =-3V,I _C =0	I _{EBO}			-10	nA
Collector-emitter cut-off current	V _{CE} =-30V,V _{BE(off)} =-0.5V	I _{CEX}			-50	nA
DC current gain	V _{CE} =-10V,I _C =-150mA	h _{FE1}	100		300	
	V _{CE} =-10V,I _C =-0.1mA	h _{FE2}	75			
	V _{CE} =-10V,I _C =-1mA	h _{FE3}	100			
	V _{CE} =-10V,I _C =-10mA	h _{FE4}	100			
	V _{CE} =-10V,I _C =-500mA	h _{FE5}	50			
Collector-emitter saturation voltage	I _C =-150mA,I _B =-15mA	V _{CE} (sat)1			-0.4	V
	I _C =-500mA,I _B =-50mA	V _{CE} (sat)2			-1.6	V
Base-emitter saturation voltage	I _C =-150mA,I _B =-15mA	V _{BE} (sat)1			-1.3	V
	I _C =-500mA,I _B =-50mA	V _{BE} (sat)2			-2.6	V
Transition frequency	V _{CE} =-20V,I _C =-50mA, f=100MHz	f _T	200			MHz
Delay time	V _{CC} =-30V, I _C =-150mA , I _{B1} =-15mA	T _d			10	nS
Rise time		Tr			25	nS
Storage time	V_{CC} =-6V, I _C =-150mA I _{B1} =-I _{B2} =-15mA	Ts			225	nS
Fall time		T _f			60	nS
				REV.3,Ja	an - 2013, K	SPR11



Electrical characteristic curves





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